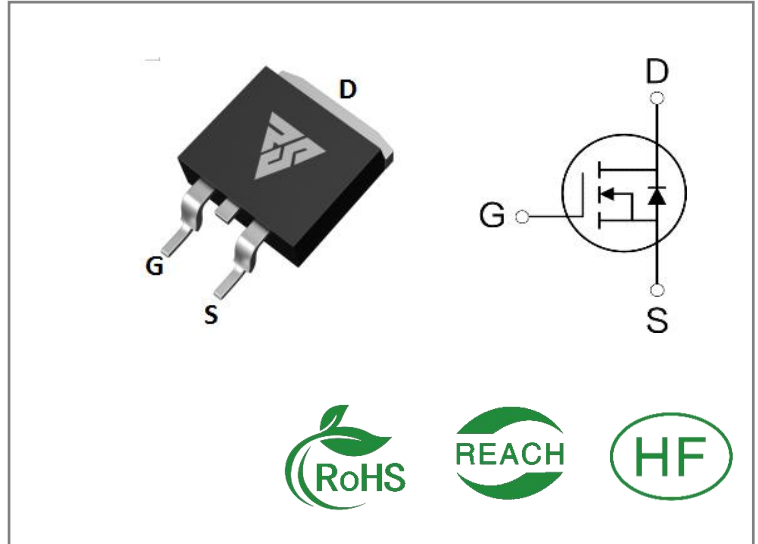


ID	R <sub>Ds(ON)</sub> (Typ)	VDSS
190A	3mΩ	100V


**Applications:**

- Load Switch
- PWM Applications
- Power Managment

**Features:**

- Fast switching speed
- 100% avalanche tested
- Improved dv/dt capability

**Ordering Information**

Part Number	Package	Marking	Packing	Qty.
RS100N190S	T0-263	RS100N190S	Tape&reel	800 PCS

**Absolute Maximun Ratings** Tc= 25°C unless otherwise specified

Symbol	Parameter	RS100N190S	Units
VDSS	Drain-to-Source Voltage	100	V
ID	Continuous Drain Current TC=25°C	190	A
ID	Continuous Drain Current TC=100°C	130	
IDM	Pulsed Drain Current	680	
PD	Power Dissipation	310	W
VGS	Gate- to- Source Voltage	±20	V
EAS	Single Pulse Avalanche Engergy L = 0.3mH, IS = 45A, RG = 25Ω, Tj = 25°C	725	mJ
TL TPKG	Maximum Temperature for Soldering	300 260	°C
	Leads at 0.063in(1.6mm)from Case for 10 seconds		
	Package Body for 10 seconds		
TJ and TSTG	Operating Junction and Storage Temperature Range	-55 to 150	

\* Drain Current Limited by Maximum Junction Temperature

Caution: Stresses greater than those listed in the“ Absolute Maximum Ratings” Table may cause permanent damage to the device.

**Thermal Resistance**

Symbol	Parameter	RS100N190S	Units	Test Conditions
R $\theta$ JC	Junction-to-Case	0.40	$^{\circ}\text{C} / \text{W}$	Drain lead soldered to water cooled heatsink, PD adjusted for a peak junction temperature of + 150 $^{\circ}\text{C}$
R $\theta$ JA	Junction-to-Ambient	45		1 cubic foot chamber, free air.

**OFF Characteristics**  $T_J = 25^{\circ}\text{C}$  unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BVDSS	Drain- to- source Breakdown Voltage	100	--	--	V	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$
IDSS	Drain- to- Source Leakage Current	--	--	1	$\mu\text{A}$	$V_{DS}=80\text{V}, V_{GS}=0\text{V}$
IGSS	Gate- to- Source Forward Leakage	--	--	100	nA	$V_{GS}=20\text{V}, V_{DS}=0\text{V}$
	Gate- to- Source Reverse Leakage	--	--	-100		$V_{GS}=-20\text{V}, V_{DS}=0\text{V}$

**ON Characteristics**  $T_J = 25^{\circ}\text{C}$  unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
RDS(on)	Static Drain- to- Source On-Resistance	--	3.0	3.6	m $\Omega$	$V_{GS}=10\text{V}, I_D=20\text{A}$
VGS(TH)	Gate Threshold Voltage	2.0	--	4.0	V	$V_{GS}=V_{DS}, I_D=250\mu\text{A}$

**Resistive Switching Characteristics** Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
td(ON)	Turn- on Delay Time	--	21	--	nS	$V_{DS}=50\text{V}$ $R_L=2.5\Omega$ $R_G=3\Omega$ $V_{GS}=10\text{V}$
trise	Rise Time	--	35	--		
td(OFF)	Turn- OFF Delay Time	--	50	--		
tfall	Fall Time	--	30	--		

**Dynamic Characteristics** Essentially independent of operating temperature

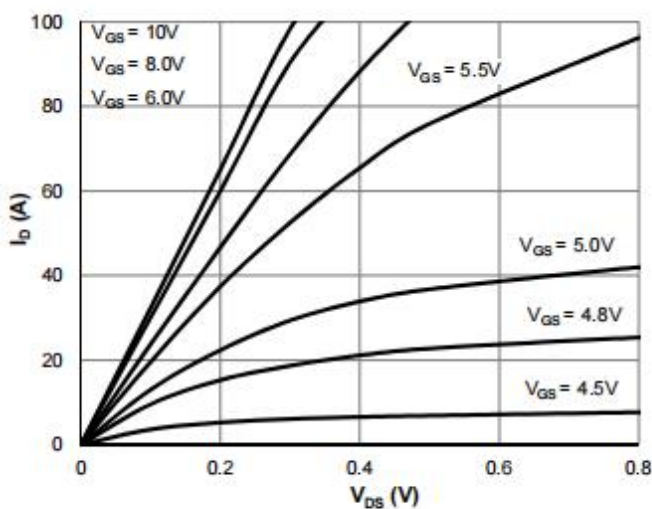
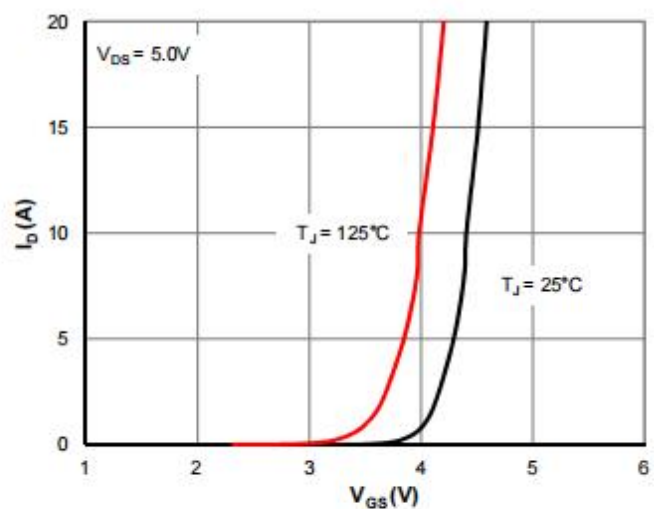
Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
Ciss	Input Capacitance	--	4790	--	pF	VGS= 0V VDS=50V f=1MHz
Coss	Output Capacitance	--	900	--		
Crss	Reverse Transfer Capacitance	--	18	--		
Qg	Total Gate Charge	--	83	--	nC	VDS= 50V ID=20A VGS=10V
Qgs	Gate- to- Source Charge	--	24	--		
Qgd	Gate-to-Drain(" Miller") Charge	--	26	--		

**Source- Drain Diode Characteristics**

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
IS	Continuous Source Current	--	--	190	A	Integral pn- diode in MOSFET
ISM	Maximum Pulsed Current	--	--	680	A	
VSD	Diode Forward Voltage	--	--	1.0	V	IS=1A,VGS=0V
trr	Reverse Recovery Time	--	70	--	nS	VGS=0V IS=20A di/dt=100A/μs
Qrr	Reverse Recovery Charge	--	125	--	nC	

**Notes:**

- \* 1. Repetitive rating,pulse width limited by maximum junction temperature.
- \* 2. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 1%

**Typical Feature Curve**

**Figure 1: Saturation Characteristics**

**Figure 2: Transfer Characteristics**

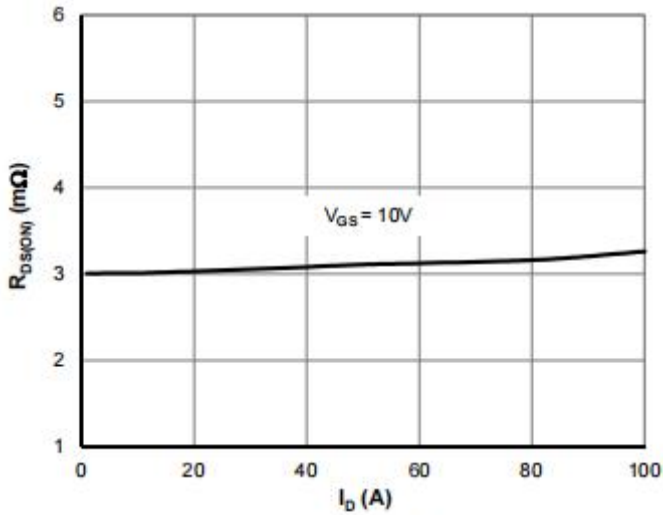


Figure 3:  $R_{DS(ON)}$  vs. Drain Current

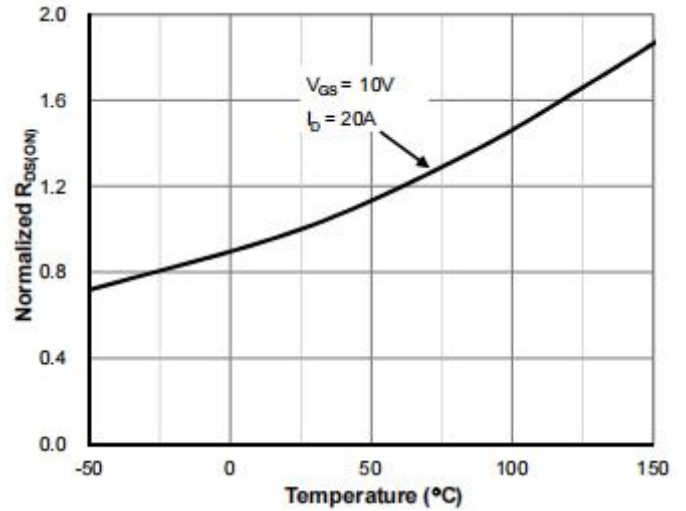


Figure 4:  $R_{DS(ON)}$  vs. Junction Temperature

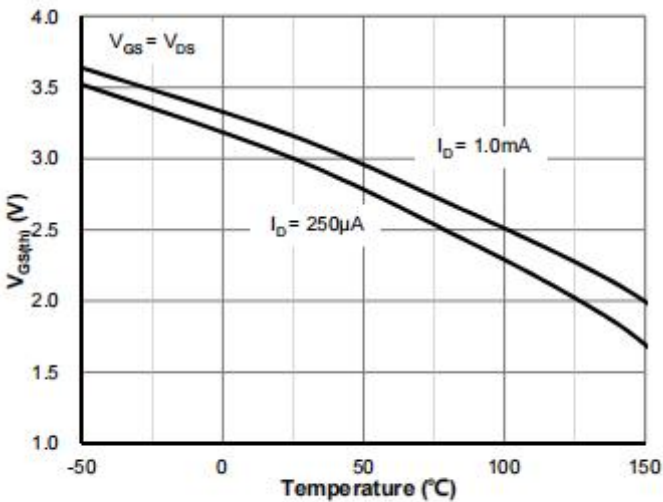


Figure 5:  $V_{GS(th)}$  vs. Junction Temperature

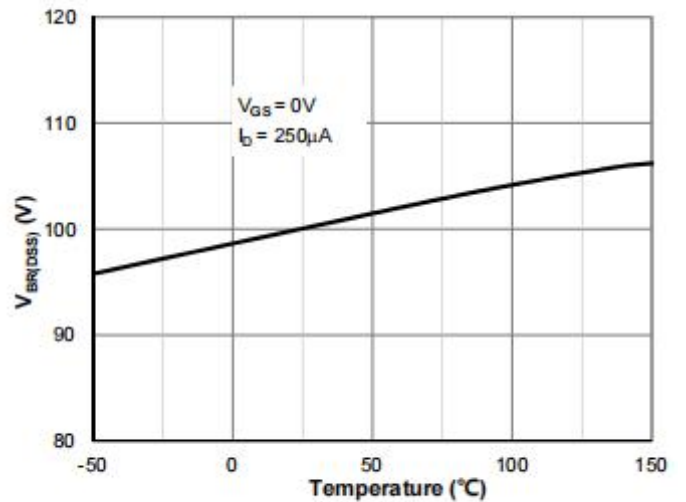


Figure 6:  $V_{BR(DSS)}$  vs. Junction Temperature

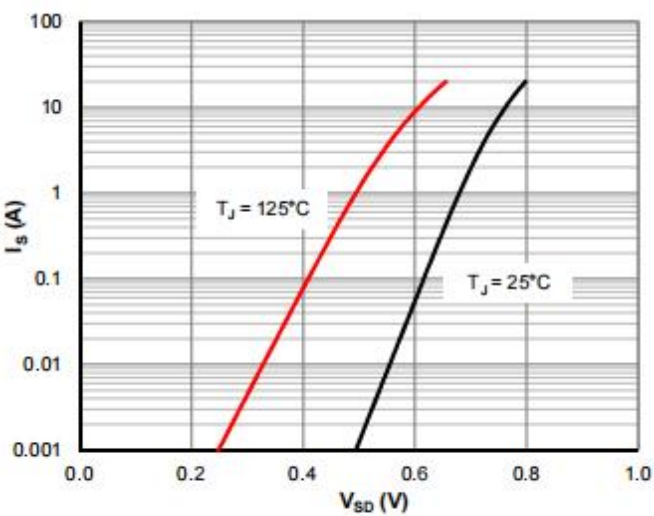


Figure 7: Body-Diode Characteristics

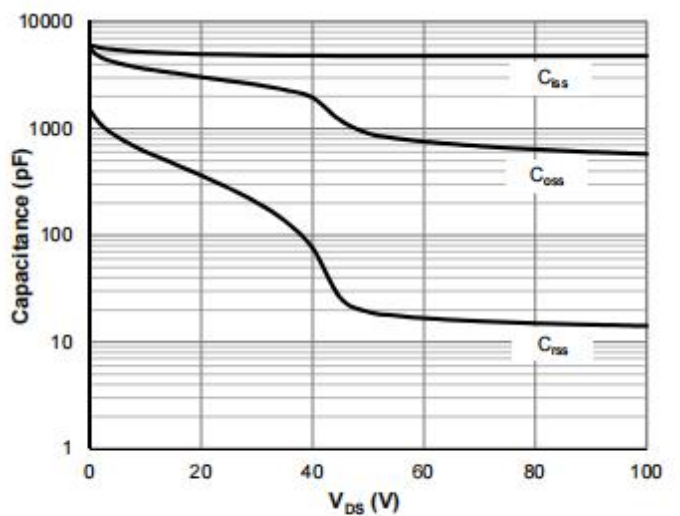


Figure 8: Capacitance Characteristics

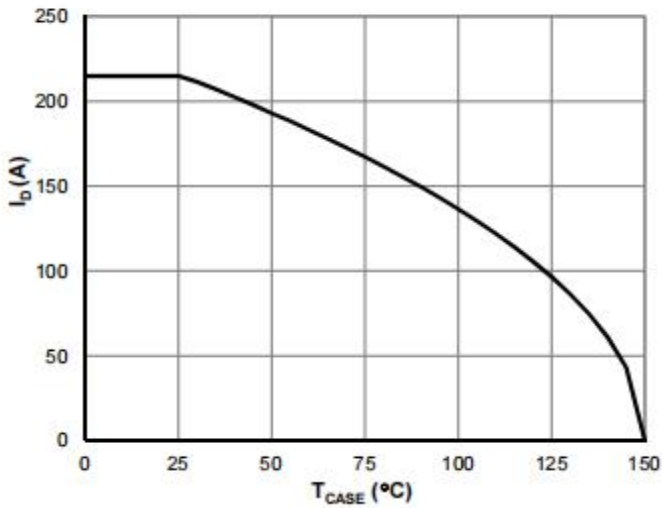


Figure 9: Current De-rating

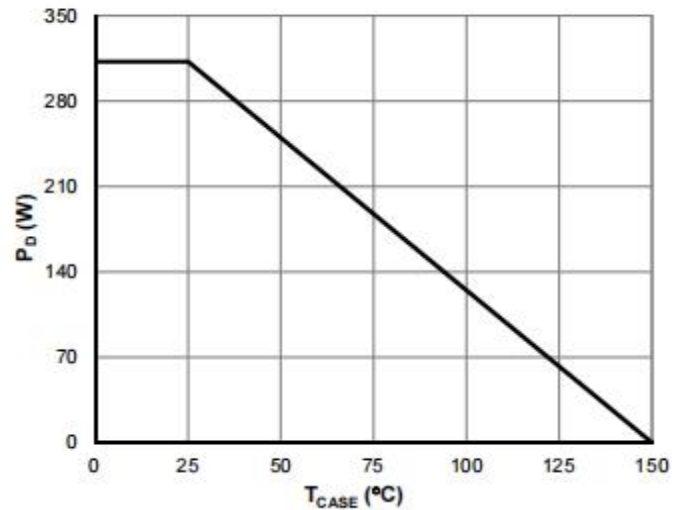


Figure 10: Power De-rating

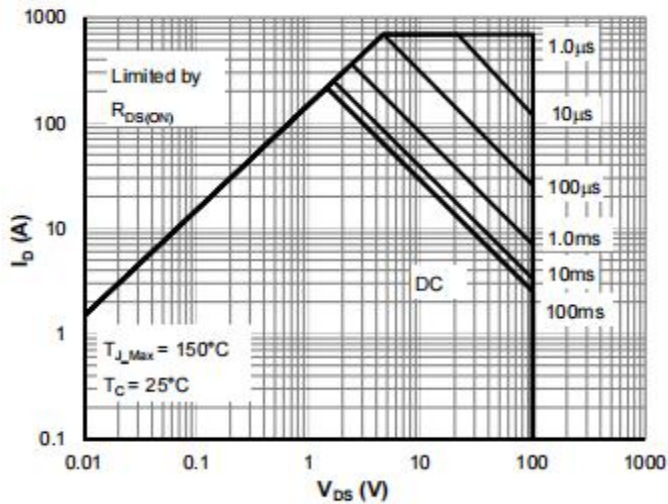


Figure 11: Maximum Safe Operating Area

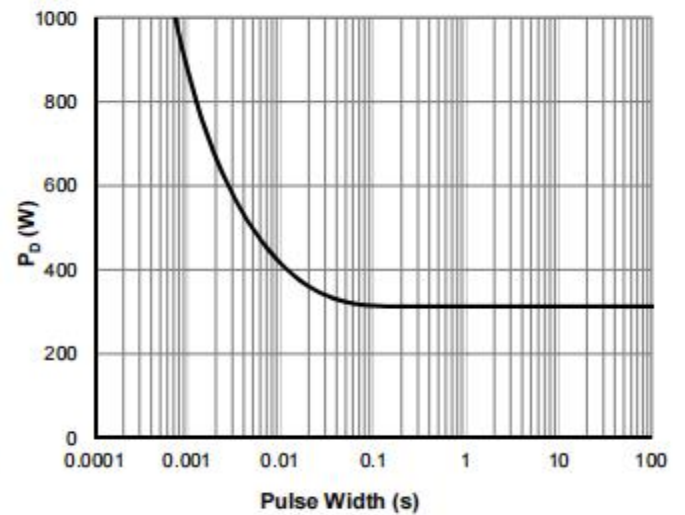


Figure 12: Single Pulse Power Rating, Junction-to-Case

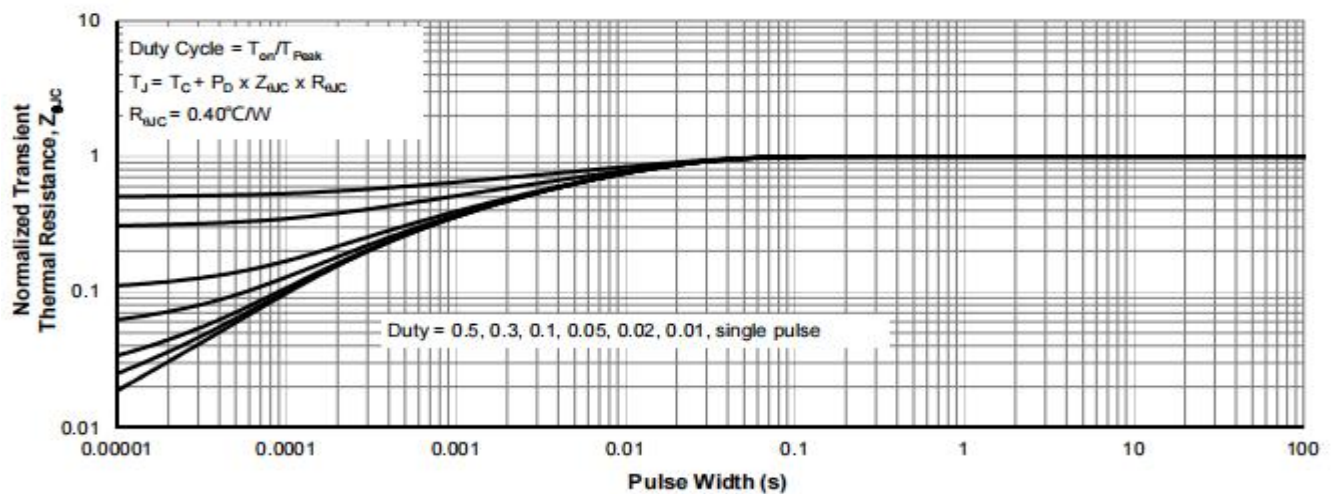


Figure 13: Normalized Maximum Transient Thermal Impedance

Test circuits and Waveforms

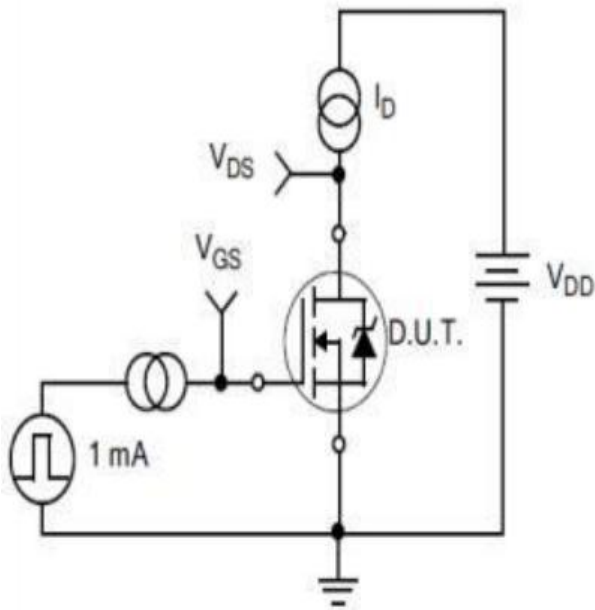


Figure A.  
Gate Charge Test Circuit

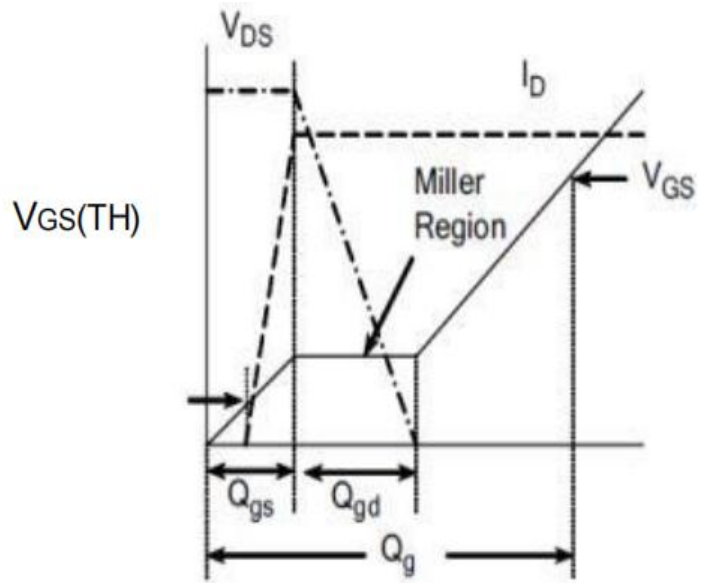


Figure B.  
Gate Charge Waveform

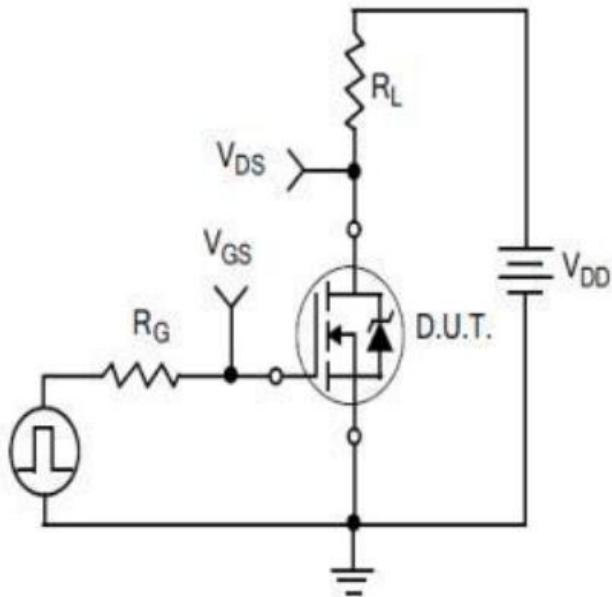


Figure C.  
Resistive Switching Test Circuit

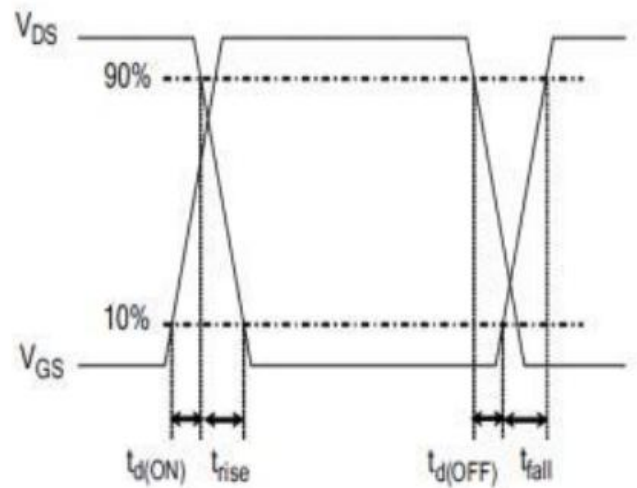


Figure D.  
Resistive Switching Waveforms

Test Circuits and Waveforms

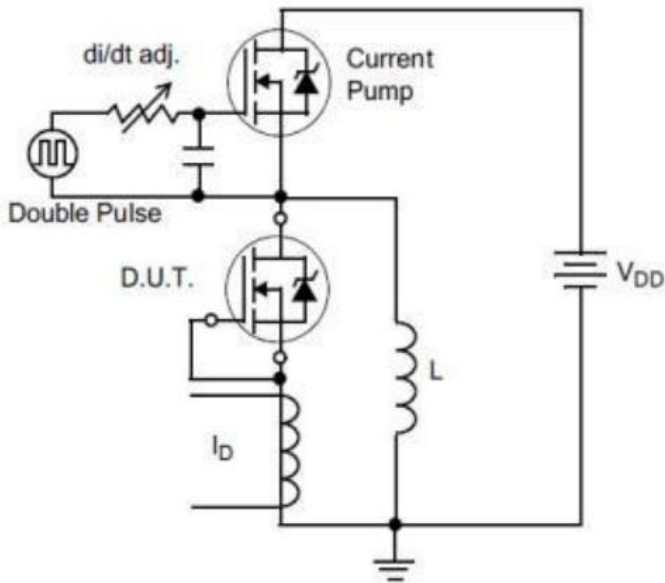


Figure E. Diode Reverse Recovery Test Circuit

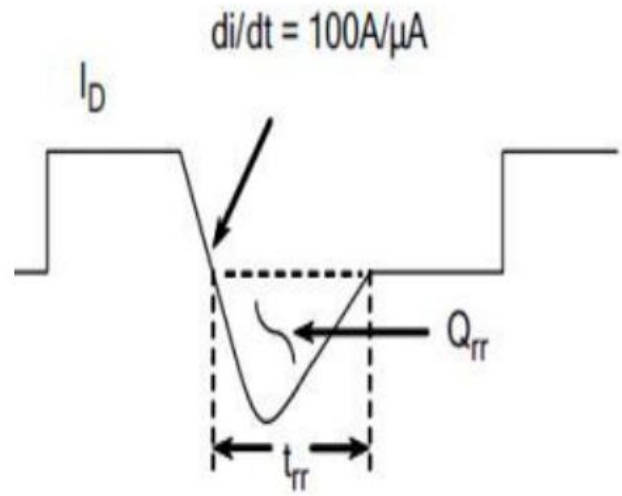


Figure F. Diode Reverse Recovery Waveform

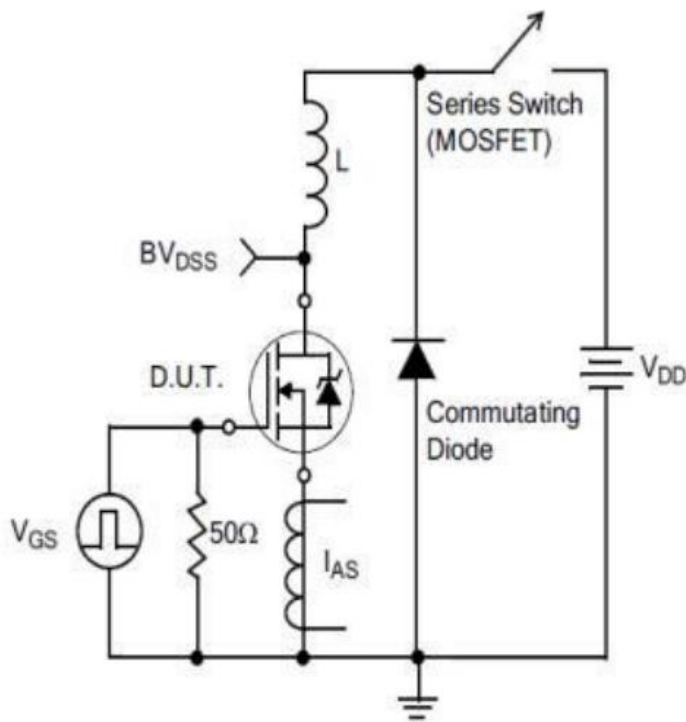
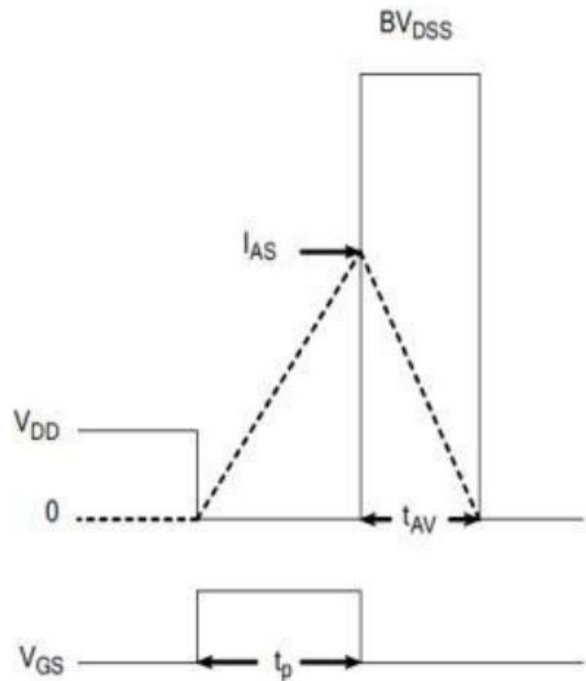


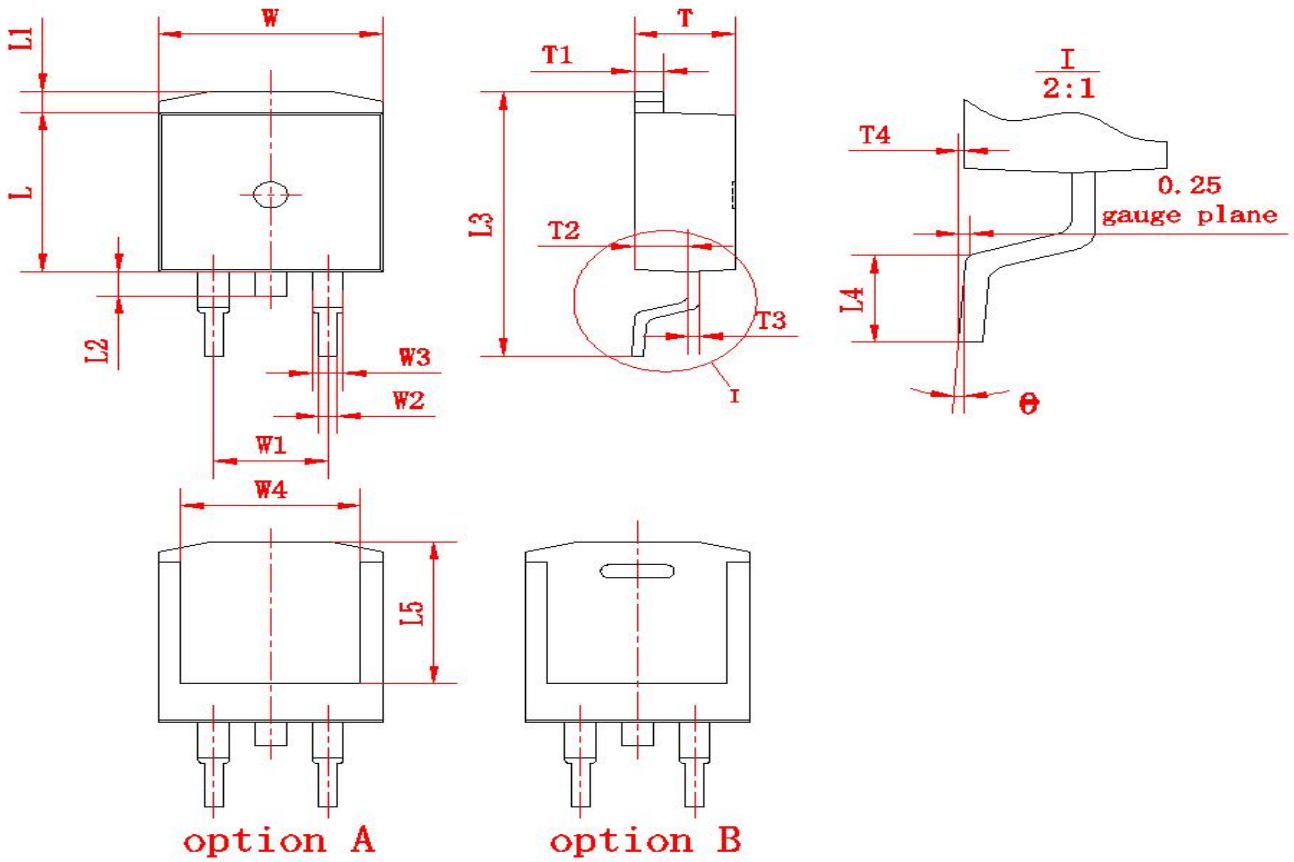
Figure G. Unclamped Inductive Switching Test Circuit



$$EAS = \frac{I_{AS}^2 L}{2}$$

Figure H. Unclamped Inductive Switching Waveforms

Package outline drawing(TO-263 Unit: mm)



(单位: mm)

符号	尺寸		符号	尺寸		符号	尺寸	
	Min	Max		Min	Max		Min	Max
W	9.80	10.20	L1	1.00	1.40	T1	1.20	1.40
W1	(5.08)		L2	1.20	1.60	T2	2.20	2.60
W2	0.70	0.95	L3	15.00	15.60	T3	0	0.25
W3	1.17	1.62	L4	2.20	2.80	T4	0	0.25
W4	(8.0)		L5	(8.2)		θ	0°	8°
L	9.00	9.40	T	4.30	4.70			



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